## **Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings of claims in the application:

## **Listing of Claims:**

- 1-9. (Canceled)
- 10. (Currently Amended) A gas supply panel comprising:
- a first mass flow controller configured to be in fluid communication with a processing gas source through a first inlet;
- a delivery line configured to be in fluid communication with the first mass flow controller and with a processing chamber through a first outlet;
- a second mass flow controller configured be in fluid communication with a carrier gas flow and with a source of silicon-containing precursor through a second inlet;
- a divert line configured to be in fluid communication with the second mass flow controller and with a chamber exhaust through a second outlet; and
- a divert valve configured to selectively place a stabilized flow of the siliconcontaining precursor vaporized in the carrier gas from the second mass flow controller in fluid communication with the delivery line or with the divert line.
- 11. (Original) The gas supply panel of claim 10 wherein the divert valve comprises a three way valve.
- 12. (Currently Amended) The gas supply panel of claim 10 further comprising a shut off valve in fluid communication with the second mass flow controller and with the second first outlet.
- 13. (Original) The gas supply panel of claim 10 further comprising a third inlet in fluid communication with the delivery line through a third mass flow controller.
- 14. (Original) The gas supply panel of claim 10 wherein the silicon-containing precursor comprises a liquid, the gas supply panel further comprising:
  - an injection valve configured to be in fluid communication with the second inlet

and with the second mass flow controller; and

a third inlet configured to be in fluid communication with a carrier gas source and with the injection valve.

- 15. (Currently Amended) A substrate processing apparatus comprising: a processing chamber including an exhaust;
- a gas distribution system configured to receive and deliver gases to a gas distribution face plate located proximate to a substrate support within the processing chamber; a gas supply panel comprising,
  - a first mass flow controller configured to be in fluid communication with a processing gas source through a first inlet,
  - a delivery line configured to be in fluid communication with the first mass flow controller and with a first outlet,
  - a second mass flow controller configured be in fluid communication with a carrier gas and with a source of silicon-containing precursor through a second inlet,
  - a divert line configured to be in fluid communication with the second mass flow controller and with a second outlet, and
  - a divert valve configured to selectively place <u>a stabilized flow of the silicon-containing precursor vaporized in the carrier gas from</u> the second mass flow controller in fluid communication with the delivery line or with the divert line:
  - a first conduit linking the first outlet with the processing chamber; and a second conduit linking the second outlet with the processing chamber exhaust.
- 16. (Original) The apparatus of claim 15 wherein the divert valve comprises a three way valve.
- 17. (Currently Amended) The apparatus of claim 15 further comprising a shut off valve in fluid communication with the second mass flow controller and with the second first outlet.

- 18. (Original) The apparatus of claim 15 further comprising a third inlet in fluid communication with the delivery line through a third mass flow controller.
- 19. (Original) The apparatus of claim 15 wherein the silicon-containing precursor comprises a liquid, the gas supply panel further comprising:

an injection valve configured to be in fluid communication with the second inlet and with the second mass flow controller; and

a third inlet configured to be in fluid communication with a carrier gas source and with the injection valve.